

MAIN CHARACTERISTICS

I_D	220A
V_{DSS}	60V
$R_{DS(on)-typ}$ (@VGS=10V Tc=25°C)	1.6mΩ

FEATURES

- SGT Power MOS
- Low RDS(on)
- Low Gate Charge

APPLICATIONS

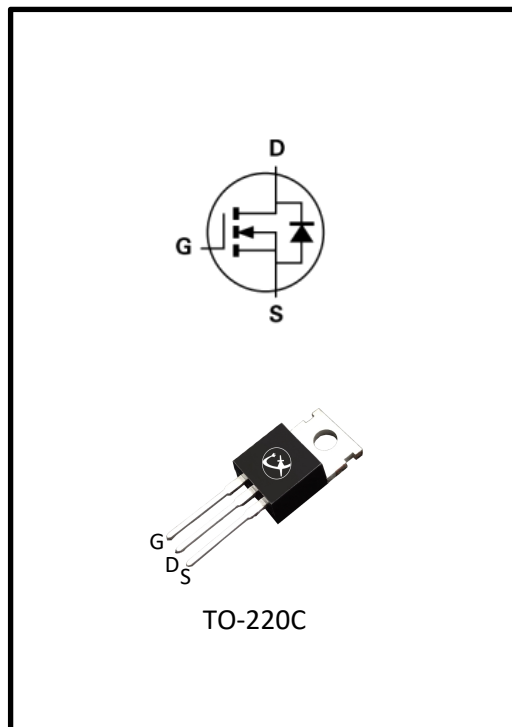
- Battery protection
- Uninterruptible Power Supply(UPS)

MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275°C maximum,10s per JESD 22-B106

Product specification classification

Part Number	Package	Mode Name	Pack
LG220N06AP	TO-220C	LG220N06AP	Tube



Maximum Ratings at Tc=25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continue Drain Current	I_D	220	A
Pulsed Drain Current (Note1)	I_{DM}	880	A
Power Dissipation	P_D	138	W
Single Pulse Avalanche Energy	E_{AS}	150	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.41	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	52	°C/W

Note1:Pulse test: 300 μ s pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	BV_{DSS}	60	-	-	V
Drain-Source Leakage Current	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	$V_{GS(th)}$	2.2	-	3.8	V
Drain-Source On-State Resistance	$V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$	$R_{DS(on)}$	-	1.6	2	m Ω
Forward Transconductance	$V_{DS} = 5 \text{ V}, I_D = 25 \text{ A}$	gfs	-	87	-	S
Input Capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$	C_{iss}	-	6970	-	pF
Output Capacitance		C_{oss}	-	1397	-	pF
Reverse Transfer Capacitance		C_{rss}	-	58	-	pF
Turn-on Delay Time(Note2)	$V_{GS}=10\text{V}, V_{DS}=30 \text{ V}, R_G=3 \Omega, I_D=50 \text{ A}$	$t_{d(ON)}$	-	15	-	ns
Rise Time(Note2)		t_r	-	27	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	62	-	ns
Fall Time(Note2)		t_f	-	50	-	ns
Total Gate Charge(Note2)	$I_D = 50 \text{ A}, V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}$	Q_G	-	97	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	34	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	18	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	220	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	880	A
Drain-Source Diode Forward Voltage	$I_{SD} = 50 \text{ A}$	V_{SD}	-	-	1.2	V
Reverse Recovery Time(Note2)	$I_{SD} = 50 \text{ A}, V_{GS} = 0 \text{ V}, dI_F / dt = 100 \text{ A}/\mu\text{s}$	trr	-	80	-	ns
Reverse Recovery Charge(Note2)		Qrr	-	115	-	nC

Note2:Pulse test: 300 μ s pulse width, 2 % duty cycle

RATINGS AND CHARACTERISTIC CURVES

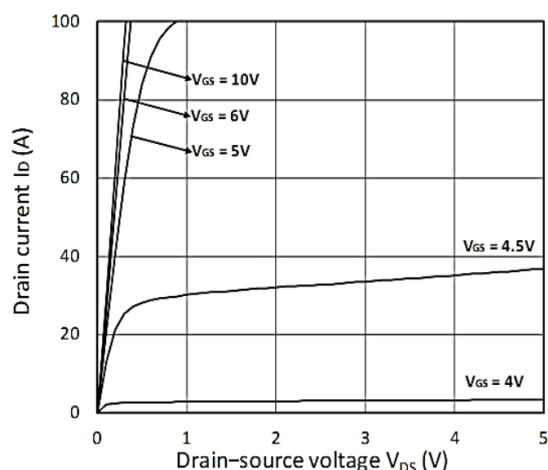


Figure 1. Output Characteristics

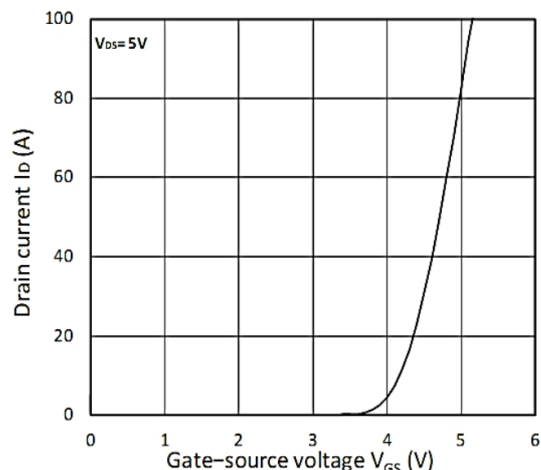


Figure 2. Transfer Characteristics

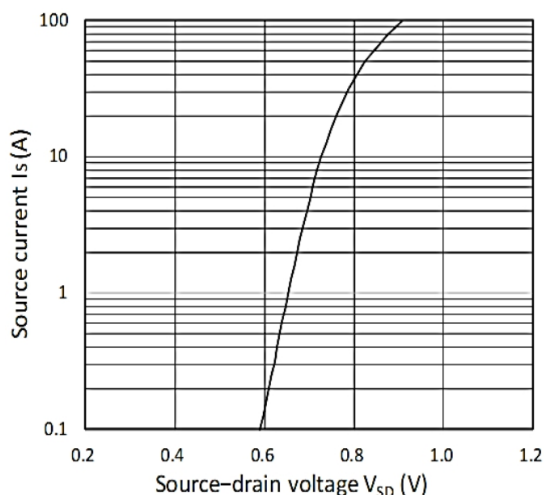


Figure 3. Forward Characteristics of Reverse

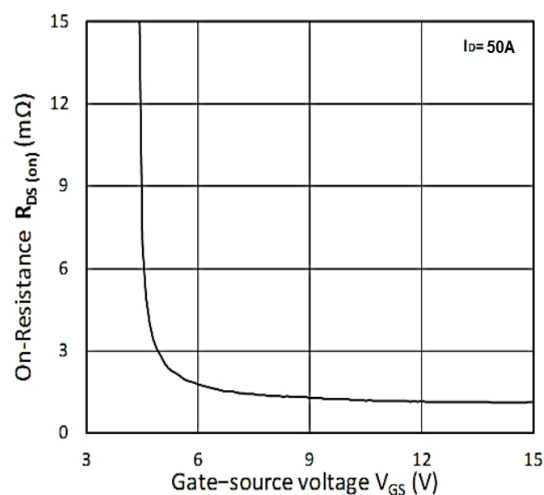


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

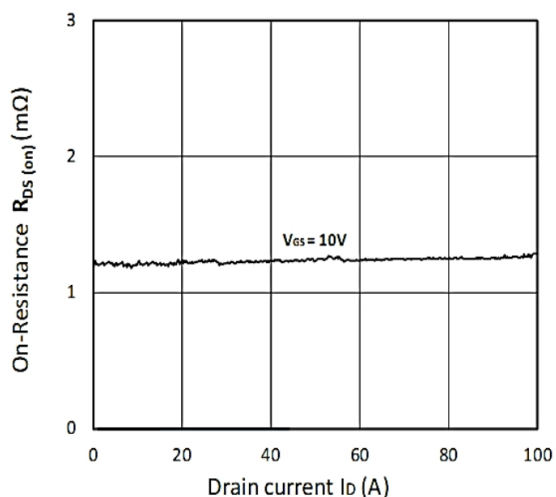


Figure 5. $R_{DS(ON)}$ vs. I_D

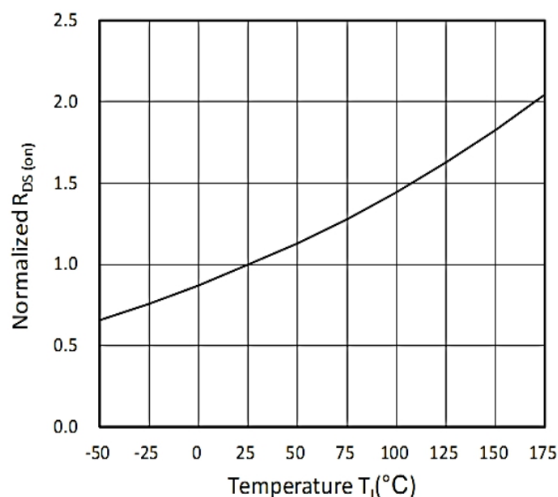


Figure 6. Normalized $R_{DS(ON)}$ vs. Temperature

RATINGS AND CHARACTERISTIC CURVES

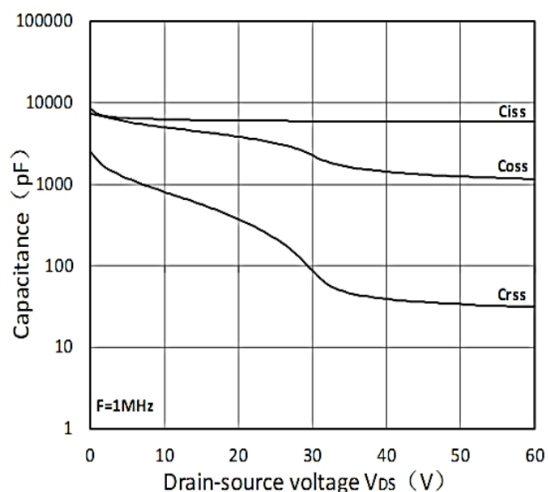


Figure 7. Capacitance Characteristics

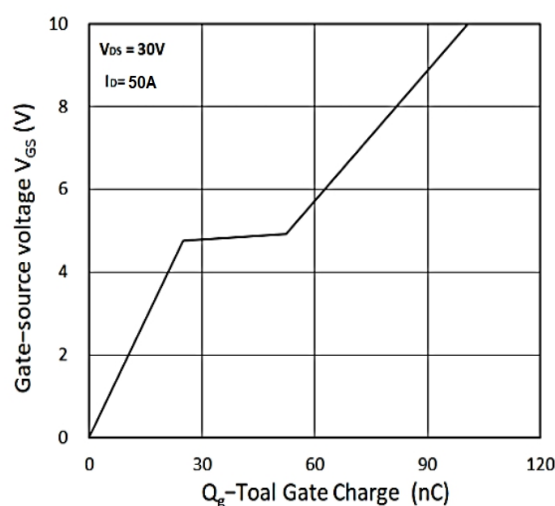


Figure 8. Gate Charge Characteristics

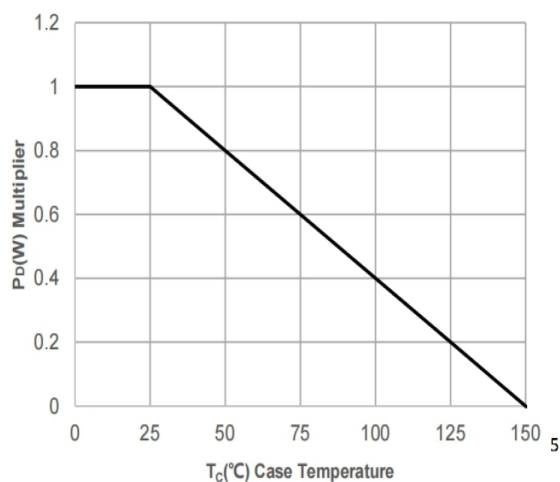


Figure 9. Power Dissipation

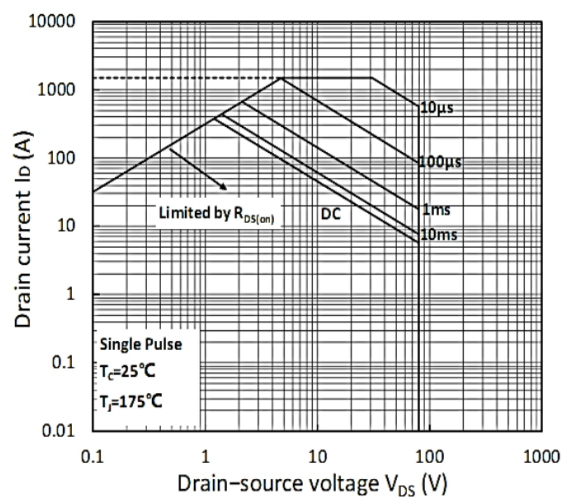


Figure 10. Safe Operating Area

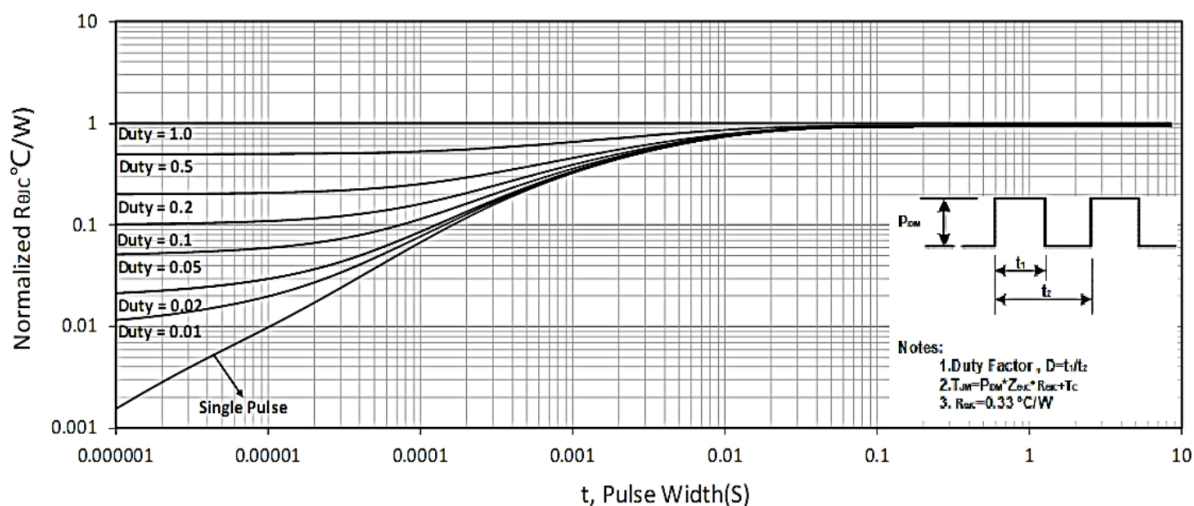
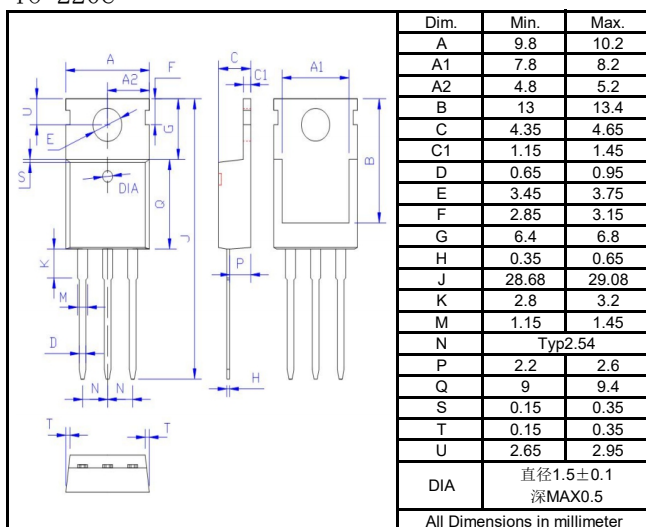


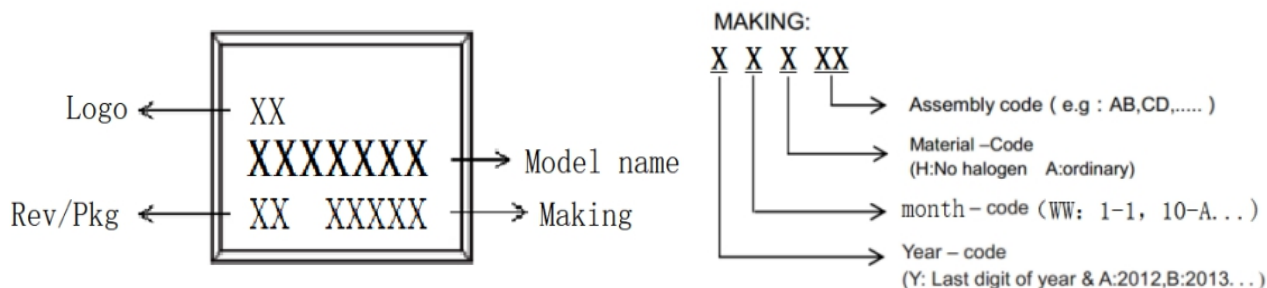
Figure 11. Normalized Maximum Transient Thermal Impedance

Package Outline Dimensions millimeters

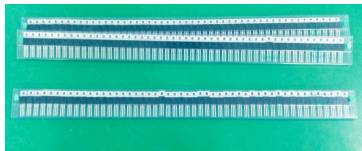
TO-220C



Marking on the body



packing instruction

PKG	Minimal Package	Mini Box	Box
TO-220C			
	50pcs/pdpe	1000pcs/box	5000pcs/box



LG220N06AP

N-Channel SGT Power MOSFET

Notice

All product, product specifications and data are subject to change without notice to improve. The right to explain is owned by LINGXUN electronics company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying power exceeding normal rated

power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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Revision History

Rev	Changes	Date
1.0	First version	2025/6/25